	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1	BRS	72	(select wirh gate) and nanocluster	USPAT; US-PGPUB	2004/09/0 1 16:10		
2	BRS	18	((select wirh gate) and nanocluster) and (nonvolatile or non adj volatile) with memory	USPAT; US-PGPUB	2004/09/0 1 16:07		
3	BRS	0	(select with gate) and nanocluster	USPAT; US-PGPUB	2004/09/0 1 16:08		
4	BRS	0	(select with gate) and nanocluster	USPAT; US-PGPUB	2004/09/0 1 16:10		
5	BRS	305	(select with gate) and nano	USPAT; US-PGPUB	2004/09/0 1 16:11		
6	BRS	0	(((select wirh gate) and nanocluster) and (nonvolatile or non adj volatile) with memory) and ((select with gate) and nano)	USPAT; US-PGPUB	2004/09/0 1 16:11		
7	BRS	20	((select with gate) and nano) and (nonvolatile or non adj volatile) with memory and cluster	USPAT; US-PGPUB	2004/09/0 1 16:17		
8	BRS	17	"5445981"	USPAT; US-PGPUB	2004/09/0 1 16:17		

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
9 BRS	114	((select with gate) and nano) and (nonvolatile or non adj volatile) with memory	USPAT; US-PGPUB	2004/09/0 1 17:18		
10 BRS	78063	(nonvolatile or non adj volatile) with memory	USPAT; US-PGPUB	2004/09/0 1 17:18		
11 BRS	3953	(nonvolatile or non adj volatile) and (memory with transistor) and (reference with transistor)	USPAT; US-PGPUB	2004/09/0 1 17:36		
12 BRS	33	(((nonvolatile or non adj volatile) with memory) and (memory with transistor) and (reference with transistor)) and (gate adj stack) and storage	USPAT; US-PGPUB	2004/09/0 1 17:19		
13 BRS	41	((nonvolatile or non adj volatile) with memory) and (memory adj transistor) and (reference adj transistor)	USPAT; US-PGPUB	2004/09/0 1 17:37		

Typ e	Hits	Search Text	DBs	Time Stamp	Comment s	Error Definit ion
14	BRS	29	(nonvolatile or (non adj volatile) with memory) and nanocluster	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 10:58		
15	BRS	307	365/185.14.ccls.	USPAT; US-PGPUB	2004/09/0 2 10:52		
16	BRS	8796	((nonvolatile or (non adj volatile) with memory) or EPROM or EEPROM or (floating with gate)) and nano$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 11:00		
17	BRS	270	(((nonvolatile or (non adj volatile) with memory) or EPROM or EEPROM or (floating with gate)) and nano$) and well and (gate with stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 11:02		
18	BRS	168	(((nonvolatile or (non adj volatile) with memory) or EPROM or EEPROM or (floating with gate)) and nano$) and well and (gate with stack)) and threshold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 15:34		

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
19 BRS	331	((nonvolatile or (non adj volatile) with memory) or EPROM or EEPROM or (floating with gate)) and (reference adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 15:35		
20 BRS	5	(((nonvolatile or (non adj volatile) with memory) or EPROM or EEPROM or (floating with gate)) and (reference adj transistor)) and (gate with stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 17:27		
21 BRS	0	(((nonvolatile or (non adj volatile) with memory) or EPROM or EEPROM or (floating with gate)) and (reference adj transistor)) and (gate adj stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 2 15:36		

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
22 BRS	10408	257/314-326.ccls. or 365/185.03,185.05,185. 14,185.18.ccls. or 438/176,190,195,200,20 1,211,216,239,241,250, 257,258,266,283.ccls.	USPAT; US-PGPUB	2004/09/0 2 17:31		
23 BRS	156	(257/314-326.ccls. or 365/185.03,185.05,185. 14,185.18.ccls. or 438/176,190,195,200,20 1,211,216,239,241,250, 257,258,266,283.ccls.) and nano	USPAT; US-PGPUB	2004/09/0 2 17:31		
24 IS&R	2	(("6088269") or ("6246607")).PN.	USPAT	2004/09/0 6 16:03		
25 IS&R	9	(("5835415") or ("5835409") or ("5768439") or ("5544103") or ("5293560") or ("4326134") or ("6093605") or ("5877980") or ("6518618")).PN.	USPAT	2004/09/0 6 16:06		

L Number	Hits	Search Text	DB	Time stamp
7	0	(memory adj array) and (storage adj material) and barrier and (conductive adj gate) and electrode and (gate adj stack)	USPAT	2004/09/06 14:35
8	0	(memory adj array) and (storage adj material) and barrier and (conductive adj gate) and electrode	USPAT	2004/09/06 14:36
9	9	(memory adj array adj cell) and storage and barrier and (conductive adj gate) and electrode	USPAT	2004/09/06 14:39
10	9	((memory adj array adj cell) and storage and barrier and (conductive adj gate) and electrode) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate)	USPAT	2004/09/06 14:43
11	1	("6088269").PN.	USPAT	2004/09/06 14:43
12	1	(("6088269").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate)	USPAT	2004/09/06 14:49
13	1	("5835415").PN.	USPAT	2004/09/06 14:49
14	1	(("5835415").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate)	USPAT	2004/09/06 14:51
15	1	(("6088269").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 14:55
16	1	("5835409").PN.	USPAT	2004/09/06 14:55
17	1	(("5835409").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 14:56
18	1	("5568439").PN.	USPAT	2004/09/06 14:56
19	1	(("5568439").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 14:56
20	1	("5544103").PN.	USPAT	2004/09/06 14:56
21	1	(("5544103").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 14:57
22	1	("5293560").PN.	USPAT	2004/09/06 14:57
23	1	(("5293560").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 14:58
24	1	("4326134").PN.	USPAT	2004/09/06 14:58

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25	1	(("4326134").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 15:07
26	220	(nonvolatile adj memory) and array and transistor and erase and threshold and voltage and storage and electrode and gate and dielectric	USPAT	2004/09/06 15:01
27	15	(nonvolatile adj memory) and array and transistor and (erase adj operation) and threshold and voltage and storage and electrode and gate and dielectric and height and program	USPAT	2004/09/06 15:06
28	1	("6246607").PN.	USPAT	2004/09/06 15:06
29	1	(("6246607").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 15:08
30	1	("6518618").PN.	USPAT	2004/09/06 15:08
31	1	(("6518618").PN.) and (memory or cell or array or dielectric or first or second or third or fourth or barrier or area or storage or material or current or electrode or gate or stack or stacked or overlying or conductive or transistor or substrate or erase or program or nonvolatile or voltage or threshold)	USPAT	2004/09/06 15:08

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